DRAM Equalization for Next-Generation DDR Technologies

Randy Wolff

DesignCon 2018 IBIS Summit

Santa Clara, California

February 2, 2018

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Agenda

- Equalization in next-generation DRAM
- JEDEC BER requirements
- Non-linearities in IBIS-AMI simulations
- Channel characterizations
- Example IBIS-AMI simulation
- IBIS-AMI model support
- Wrap-up



Equalization in Next-Generation DRAM

- DDR systems are implementing equalization techniques in DRAM and controllers to improve SI at higher data rates
 - DDR4 @ 3200 Mbps
 - DDR5 @ 4000+ Mbps
 - GDDR6
- Many controllers have implemented TX FFE and RX CTLE in DDR4
- DRAM may have vendor-specific implementations of CTLE and/or DFE in DDR4 and JEDEC-specified DFE in DDR5
- IBIS-AMI or AMI-like simulation techniques may be needed to include equalization in simulation results



Are SerDes Analysis Techniques Required by JEDEC?

- Some confusion exists about BER definitions in the DDR4 JEDEC spec
 - JEDEC: "The input buffer design specification is to achieve at least a BER = E-16 when the RxMask is not violated. The BER will be characterized and extrapolated if necessary using a dual-Dirac method from a higher BER (tbd)."
 - The BER is from the DRAM, not System perspective.
 - This does not mean the system needs to be simulated to 1E-16 BER
- What BER do you need to simulate to? Depends on your system requirement.
- Low BER modeling not enabled in DDR4, since RJ not defined for DRAM
 - May change with RJ spec'd for DDR5



Capturing Non-linearities in IBIS-AMI Simulations

- AMI simulation will characterize a channel (typically with a rising step response) to create an impulse response (IR)
- What non-linearities can be captured in the IR?
 - Non-linear I-V of on-die termination and output driver
 - Only ringing characteristics of 0-to-1 transition, not 1-to-0 transition
 - Non-linear characteristics of pulldown to pullup transition captured in IBIS [Model] V-t waveform



2-DIMM 1-rank DDR4 channel Impulse Response



Capturing Non-linearities

- Which non-linearities are not captured with rising step response?
 - Imbalanced pulldown/pullup behavior
 - Overshoot characteristics of pulldown (not actual pre-emphasis), so can't be modeled as FFE
 - SSO noise effects that may add significant jitter and voltage margin degradation

Imbalanced Pullup/Pulldown Transition Behavior







Channel Characterization Options

- Time Domain waveform from rising step channel characterization shown on right
- Mismatch seen in 0's
- Other options may be available in simulators
 - Rise/fall
 - PRBS
 - ?

Blue – Channel simulation Red – IBIS time domain simulation





Channel Characterization Options

- PRBS-based channel characterization with same stimuli as time domain
- Shows some improvement in 0's
- What correlation is acceptable?
 - TBD

Blue – Channel sim Red – IBIS time domain sim





Example IBIS-AMI Simulation with DFE

- 2-DIMM, 1-rank @3200 Mbps
- Non-optimized termination to increase reflections
- IBIS-AMI model of 3-tap DFE improves eye height from 0.218mV to 0.317mV (+99mV)





IBIS-AMI Modeling Support

IBIS-AMI models for DRAM equalization have limited support

- Two EDA vendors supporting IBIS-AMI for DDR simulation
- Some EDA vendors supporting AMI-like channel simulation flows with non-AMI custom solutions
- Some EDA vendors supporting traditional IBIS simulation flows for DDR simulation with equalization post-processing techniques



Wrap-up

- Equalization techniques used in SerDes interfaces have come to singleended signaling interfaces
- Multiple simulation techniques may be needed to characterize non-linear effects seen in single-ended signals (SSO)
 - Traditional time domain and IBIS-AMI type
- What do DRAM and controller vendors do now to support DDR system simulations?
 - May need to support IBIS-AMI, IBIS, and custom models for each customer based on the EDA software they use
 - Deja-vu of IBIS-AMI for SerDes circa 2007
 - Continuing dialog needed between model creators, EDA vendors, and system designers to enable a better solution



